

# MA3Z792D

## Silicon epitaxial planar type

For super-high speed switching circuit

For small current rectification

### ■ Features

- Two MA3Z792s diodes (anode common) are contained in the S-mini type 3-pin package
- Allowing to rectify under ( $I_{F(AV)} = 100 \text{ mA}$ ) condition
- Optimum for high-frequency rectification because of its short reverse recovery time ( $t_{rr}$ )
- Low  $V_F$  (forward rise voltage), with high rectification efficiency

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	30	V
Repetitive peak reverse voltage	$V_{RRM}$	30	V
Peak forward current	Single	$I_{FM}$	300
	Double* <sup>2</sup>		200
Average forward current	Single	$I_{F(AV)}$	100
	Double* <sup>2</sup>		70
Non-repetitive peak forward surge current* <sup>1</sup>	$I_{FSM}$	1	A
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

Note) \*1 : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

\*2 : Value per chip

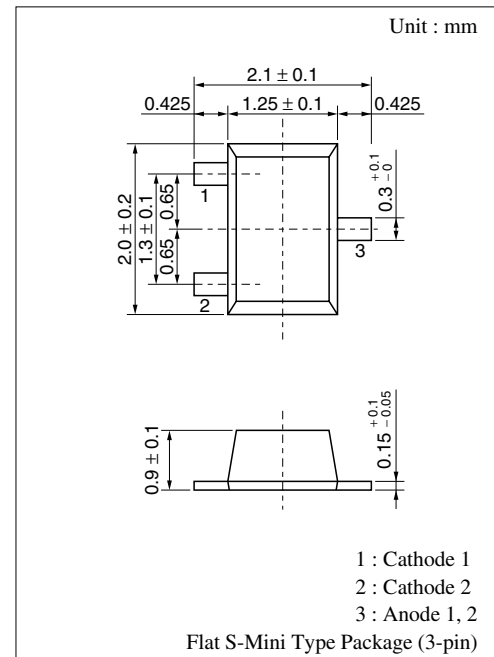
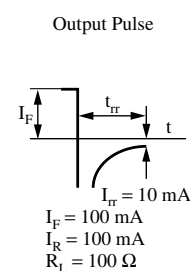
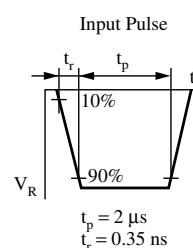
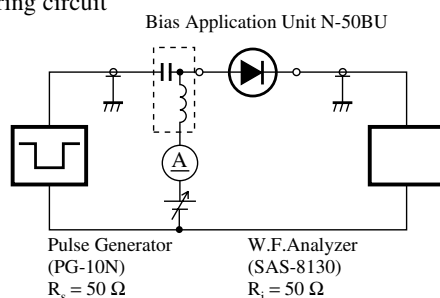
### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 30 \text{ V}$			15	$\mu\text{A}$
Forward voltage (DC)	$V_F$	$I_F = 100 \text{ mA}$			0.55	V
Terminal capacitance	$C_t$	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$		20		pF
Reverse recovery time*	$t_{rr}$	$I_F = I_R = 100 \text{ mA}$ $I_{rr} = 10 \text{ mA}, R_L = 100 \Omega$		2		ns

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

2. Rated input/output frequency: 250 MHz

3. \* :  $t_{rr}$  measuring circuit



Marking Symbol: M3Y

Internal Connection

